

**AMENDMENTS TO THE CLAIMS**

Please cancel claims 11-20 without prejudice, and add new claims 41-51, such that the status of the claims is as follows:

1. (Original) A light emitting diode (LED), comprising:  
a semiconductor layer of a first polarity;  
an active layer, located on the semiconductor layer of the first polarity; and  
a semiconductor layer of a second polarity, located on the active layer, wherein at least one side of at least the active layer and the semiconductor layer of the second polarity is of irregular shape, thereby reducing the probability of reflecting the light emitted from the active layer, thus making light emitted from the active layer penetrate through the at least one side and be emitted outside the LED.
2. (Original) The LED according to claim 1, wherein the semiconductor layer of the first polarity is made of GaN.
3. (Original) The LED according to claim 1, wherein the active layer is made of InGaN.
4. (Original) The LED according to claim 1, wherein the semiconductor layer of the second polarity is made of GaN.
5. (Original) The LED according to claim 1, wherein the shape of the at least one side is selected from a group consisting of triangle, semicircle, and parabola.

6. (Original) The LED according to claim 1, wherein a deformed dimension of the at least one side is greater than an equivalent emitting wavelength of the LED.

7. (Original) The LED according to claim 1, wherein an incident angle of the light emitted from the active layer to the at least one side is less than a reflective critical angle of the at least one side.

8. (Original) The LED according to claim 1, wherein at least the active layer and the semiconductor layer of the second polarity therein further have at least one valley penetrating from an upper surface of the semiconductor layer of the second polarity to a lower surface of the active layer, thereby increasing an efficiency of emitting the light emitted from the active layer to the outside of the LED.

9. (Original) The LED according to claim 8, further comprising a substrate located under the semiconductor layer of the first polarity, wherein the at least one valley further reaches to an upper surface of the substrate.

10. (Original) The LED according to claim 1, wherein the at least one side is formed by reactive ion etching (RIE).

11 - 40. (Canceled).

41. (New) A light emitting diode (LED), comprising:  
a semiconductor layer of a first polarity;  
an active layer, located on the semiconductor layer of the first polarity; and  
a semiconductor layer of a second polarity, located on the active layer;

wherein at least the semiconductor layer of the second polarity has a geometry configured to reduce the probability of reflecting the light emitted from the active layer, thus making light emitted from the active layer penetrate through at least one side of the semiconductor layer of the second polarity and be emitted outside the LED with increased efficiency.

42. (New) The LED according to claim 41, wherein the at least one side of the semiconductor layer of the second polarity is of irregular shape.
43. (New) The LED according to claim 42, wherein the shape of the at least one side of the semiconductor layer of the second polarity is selected from a group consisting of triangle, semicircle, and parabola.
44. (New) The LED according to claim 42, wherein a deformed dimension of the at least one side of the semiconductor layer of the second polarity is greater than an equivalent emitting wavelength of the LED.
45. (New) The LED according to claim 42, wherein an incident angle of the light emitted from the active layer to the at least one side of the semiconductor layer of the second polarity is less than a reflective critical angle of the at least one side.
46. (New) The LED according to claim 42, wherein the at least one side of the semiconductor layer of the second polarity is formed by reactive ion etching (RIE).

47. (New) The LED according to claim 41, wherein at least the active layer and the semiconductor layer of the second polarity have at least one valley penetrating from an upper surface of the semiconductor layer of the second polarity to a lower surface of the active layer.

48. (New) The LED according to claim 47, further comprising a substrate located under the semiconductor layer of the first polarity, wherein the at least one valley further reached to an upper surface of the substrate.

49. (New) The LED according to claim 41, wherein the semiconductor layer of the first polarity is made of GaN.

50. (New) The LED according to claim 41, wherein the active layer is made of InGaN.

51. (New) The LED according to claim 41, wherein the semiconductor of the second polarity is made of GaN.